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ABSTRACT

In order to improve the characteristics of the high breakdown
voltage MOS transistor, a semiconductor device of the present
invention is characterized in that an LDMOS transistor, which
5 comprises a source region 4, a channel region 8, and a drain region
5, and a gate electrode 7 formed on the channel region 8, and a drift
region formed between the channel region 8 and the drain region 5,
wherein an N⁻-type low concentration layer 22 serving as the drift
region is formed shallowly at least below the gate electrode 7 (first
10 N⁻-type layer 22A) but formed deeply in a neighborhood of the drain
region 5 (second N⁻-type layer 22B).